

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT(S):	Shen et al.	CONF. NO.:	1665
SERIAL NO.:	10/582,035	GROUP NO.:	4146
FILING DATE:	May 7, 2007	EXAMINER:	Huber, Robert T.
TITLE:	MONOLITHIC POWER SEMICONDUCTOR STRUCTURES		

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
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AMENDMENT AND RESPONSE

This paper responds to the Office Action mailed on February 25, 2008, in the above-identified patent application.

Please amend the above-identified patent application as follows, without prejudice:

- **Amendments to the specification** begins on page 2 of this paper;
- **Listing of claims** begins on page 3 of this paper; and
- **Remarks** begin on page 9 of this paper.

Amendments to the Specification

Please amend the title as follows:

Monolithic Power Semiconductor Structures Including Pairs of Integrated Devices

Please re-write paragraph [0029] as indicated below:

[0029] FIG. 9 depicts a ~~second~~seventh aspect of the present invention in accordance with the teachings presented herein.

Please re-write the Abstract as indicated below:

~~Provided herein are exemplary embodiments of a~~ Monolithic semiconductor structures having at least ~~two pairs of~~ two lateral constructed semiconductor devices combined on a first surface of a single semiconductor substrate. Embodiments include connected source terminals defining common source terminals.